



<u>MMDT3906V</u>

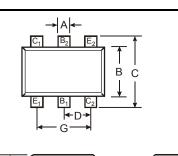
DUAL PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

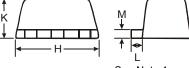
Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 20
- Terminals: Lead bearing terminal plating available. See Ordering information Page 3
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)







SOT-563									
Dim	Min Max Typ								
Α	0.15	0.30	0.25						
в	1.10	1.20							
С	1.55 1.70 1.60								
D	0.50								
G	0.90	1.10	1.00						
H	1.50 1.70 1.60								
к	0.56 0.60 0.60								
L	0.10 0.30 0.20								
М	0.10	0.18	0.11						
All I	All Dimensions in mm								

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-40	V	
Collector-Emitter Voltage	V _{CEO}	-40	V	
Emitter-Base Voltage	V _{EBO}	-5.0	V	
Collector Current - Continuous	Ι _C	-200	mA	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 3) @ T _A = 25°C	Pd	150	mW
Thermal Resistance, Junction to Ambient	(Note 3) @ T _A = 25°C	$R_{ ext{ heta}JA}$	833	°C/W
Operating and Storage Temperature Range		Tj, T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

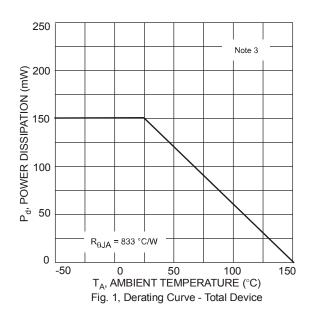
 Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

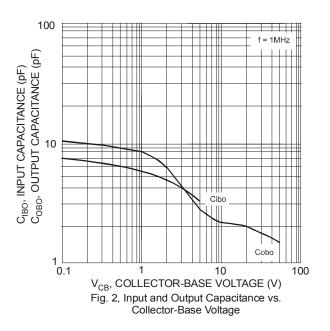


Electrical Characteristics @T_A = 25°C unless otherwise specified

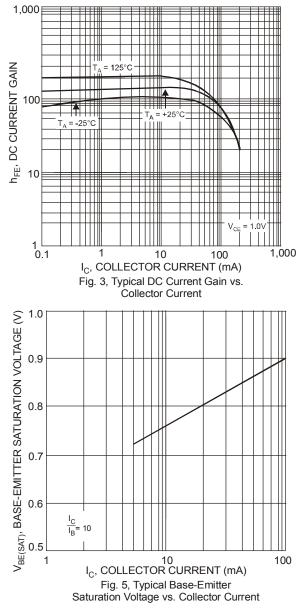
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	1 -			1	1
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	_	V	$I_{\rm C} = -10 \mu {\rm A}, \ I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40	_	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	_	V	$I_{\rm E}$ = -10µA, $I_{\rm C}$ = 0
Collector Cutoff Current	I _{CEX}	_	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
Base Cutoff Current	I _{BL}	_	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
ON CHARACTERISTICS (Note 6)	·			•	•
DC Current Gain	h _{FE}	60 80 100 60 30	 300 	_	$\begin{split} I_{C} &= -100 \mu A, \ V_{CE} &= -1.0 V \\ I_{C} &= -1.0 m A, \ V_{CE} &= -1.0 V \\ I_{C} &= -10 m A, \ V_{CE} &= -1.0 V \\ I_{C} &= -50 m A, \ V_{CE} &= -1.0 V \\ I_{C} &= -100 m A, \ V_{CE} &= -1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-0.25 -0.40	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65	-0.85 -0.95	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	_	4.5	pF	V _{CB} = -5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	Cibo	_	10	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	2.0	12	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,
Small Signal Current Gain	h _{fe}	100	400	—	f = 1.0kHz
Output Admittance	h _{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	f _T	250	—	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Noise Figure	NF		4.0	dB	V _{CE} = -5.0V, I _C = -100μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS	•				
Delay Time	t _d		35	ns	V _{CC} = -3.0V, I _C = -10mA,
Rise Time	tr	_	35	ns	$V_{BE(off)}$ = 0.5V, I _{B1} = -1.0mA
Storage Time	ts	_	225	ns	V _{CC} = -3.0V, I _C = -10mA,
Fall Time	t _f		75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

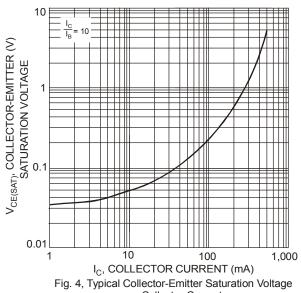
Notes: 6. Short duration pulse test used to minimize self-heating effect.











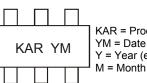
vs. Collector Current

Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT3906V-7	SOT-563	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



KAR = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Year	2005		2006	2007		2008	2009		2010	2011		2012
Code	S		Т	U		V	W		Х	Y		Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



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